





N-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

BV _{DSS}	Rds(on) max	I _{D MAX} T _A = +25°C
30V	38mΩ @ V _{GS} = 10V	5.8A
307	$64m\Omega @ V_{GS} = 4.5V$	4.5A

Description

This new generation MOSFET is designed to minimize the on-state resistance $(R_{DS(ON)})$ and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

Applications

- Load Switch
- DC-DC Converters
- Power Management Functions

Features and Benefits

- Low On-Resistance
- Low Gate Threshold Voltage
- Low Input Capacitance
- · Fast Switching Speed
- Low Input/Output Leakage
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)

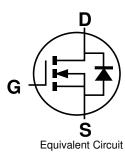
Mechanical Data

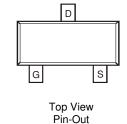
- Case: SOT23
- Case Material: Molded Plastic, "Green" Molding Compound.
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 (3)
- Terminal Connections: See Diagram
- Weight: 0.008 grams (Approximate)

SOT23



Top View





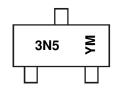
Ordering Information (Note 4)

Part Number	Case	Packaging
DMN3051L-7	SOT23	3000/Tape & Reel

Notes: 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.

- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/

Marking Information



3N5 = Product Type Marking Code YM = Date Code Marking Y or \overline{Y} = Year (ex: G = 2019) M = Month (ex: 9 = September)

Date Code Kev

Date Code Ney												
Year	200	07	~	2019	2020) 2	2021	2022	2023	20	24	2025
Code	U	l	~	G	Н		I	J	K		L	М
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
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Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristi	Symbol	Value	Unit			
Drain-Source Voltage	V_{DSS}	30	V			
Gate-Source Voltage	V_{GSS}	±20	V			
	Steady State	T _A = +25°C	I _D	4.5	Α	
Continuous Drain Current (Note 6) V 10V	Sleady State	T _A = +70°C		3.5		
Continuous Drain Current (Note 6) V _{GS} = 10V	t<5s	T _A = +25°C	1	5.8	۸	
	1<35	T _A = +70°C	l _D	4.9	А	
Pulsed Drain Current (10µs Pulse, Duty Cycle =	I _{DM}	20	Α			
Maximum Body Diode Forward Current (Note 6)	I _S	2	Α			

Thermal Characteristics

Characteristic	Symbol	Value	Unit	
Total Power Dissipation (Note 5)	$T_A = +25$ °C	Pn	0.7	W
Total Fower Dissipation (Note 3)	$T_A = +70$ °C	Pυ	0.44	
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	ר	182	°C/W
Thermal Resistance, sunction to Ambient (Note 5)	t < 5s	$R_{ heta JA}$	109	
Total Power Dissipation (Note 6)	$T_A = +25$ °C	0	1.4	W
Total Fower Dissipation (Note o)	$T_A = +70$ °C	P_D	0.85	
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	0	94	°C/W
Thermal Resistance, sunction to Ambient (Note 6)	t < 5s	$R_{ heta JA}$	56	
Thermal Resistance, Junction to Case (Note 6)	$R_{ heta JC}$	25		
Operating and Storage Temperature Range		T _{J,} T _{STG}	-55 to +150	°C

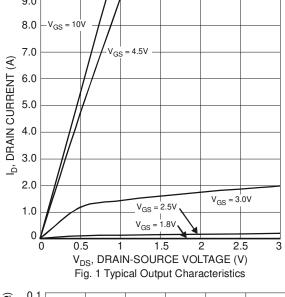
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

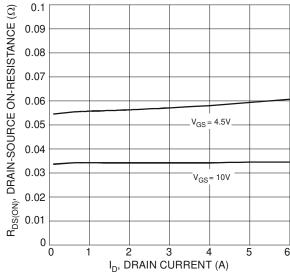
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)						
Drain-Source Breakdown Voltage	BV _{DSS}	30	_	_	V	$V_{GS} = 0V, I_D = 250\mu A$
Zero Gate Voltage Drain Current	I _{DSS}	_	_	800	nA	$V_{DS} = 28V, V_{GS} = 0V$
Gate-Body Leakage	I _{GSS}	_	-	±80	- nA	$V_{GS} = \pm 12V, V_{DS} = 0V$
Cale-body Leakage	IGSS			±800		$V_{GS} = \pm 20V$, $V_{DS} = 0V$
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	V _{GS(TH)}	1.3	1.9	2.2	V	$V_{DS} = V_{GS}$, $I_D = 250 \mu A$
Static Drain-Source On-Resistance	Б	_	33	38	0	$V_{GS} = 10V, I_D = 5.8A$
Static Drain-Source On-Resistance	R _{DS(ON)}		54	64	mΩ	$V_{GS} = 4.5V, I_D = 5.0A$
Forward Transconductance	Y _{fs}	_	5	_	S	$V_{DS} = 5V, I_D = 3.1A$
Source-Drain Diode Forward Voltage	V_{SD}	_	0.78	1.16	V	$V_{GS} = 0V, I_{S} = 2.0A$
DYNAMIC CHARACTERISTICS (Note 8)						
Input Capacitance	C _{iss}	_	424	_	pF	
Output Capacitance	Coss	_	115	_	pF	$V_{DS} = 5V$, $V_{GS} = 0V$ f = 1.0MHz
Reverse Transfer Capacitance	C_{rss}	_	81	_	pF	1 - 1.00012
Gate Resistance	Rg	_	1.51	_	Ω	$V_{DS} = 0V$, $V_{GS} = 0V$, $f = 1MHz$
Total Gate Charge	Qg	_	9.0	_	nC	
Gate-Source Charge	Q _{gs}	_	1.3	_	nC	$V_{GS} = 10V, V_{DS} = 15V, I_D = 5.8A$
Gate-Drain Charge	Q_{gd}	_	1.3	_	nC	
Turn-On Delay Time	t _{D(ON)}	_	3.4	_	ns	
Turn-On Rise Time	t _R	_	6.2	_	ns	V _{DD} = 15V, V _{GS} = 10V,
Turn-Off Delay Time	t _{D(OFF)}	_	13.9	_	ns	$R_L = 2.6\Omega$, $R_g = 3\Omega$
Turn-Off Fall Time	t _F	_	2.8	— ns		7

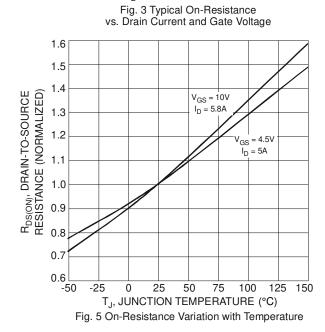
Notes:

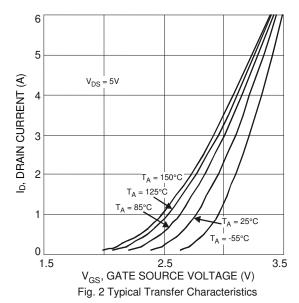
^{5.} Device mounted on FR-4 PCB with minimum recommended pad layout, single sided.
6. Device mounted on 1" x 1" FR-4 PCB with high coverage 2 oz. Copper, single sided.
7. Short duration pulse test used to minimize self-heating effect.
8. Guaranteed by design. Not subject to production testing.

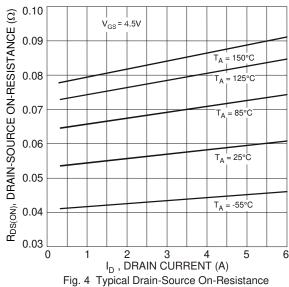


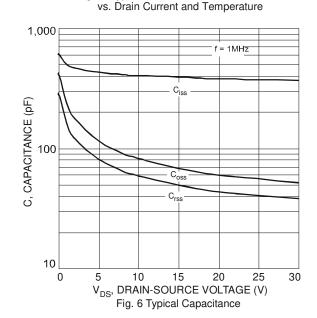














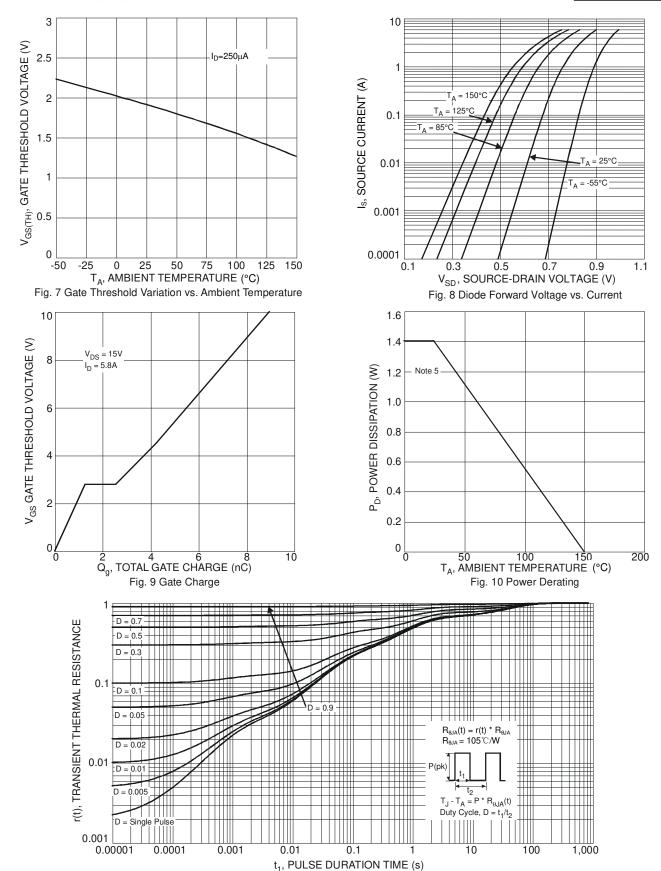
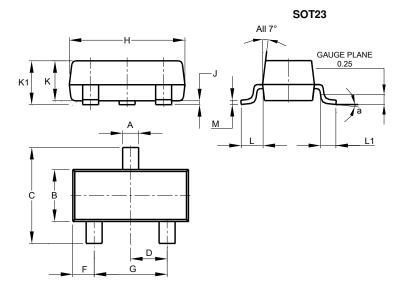


Fig. 11 Transient Thermal Response



Package Outline Dimensions

 $Please see \ http://www.diodes.com/package-outlines.html \ for the \ latest \ version.$

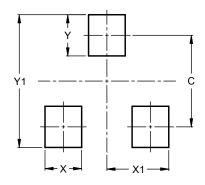


	SOT23						
Dim	Min	Max	Тур				
Α	0.37	0.51	0.40				
В	1.20	1.40	1.30				
С	2.30	2.50	2.40				
D	0.89	1.03	0.915				
F	0.45	0.60	0.535				
G	1.78	2.05	1.83				
Н	2.80	3.00	2.90				
J	0.013	0.10	0.05				
K	0.890	1.00	0.975				
K1	0.903	1.10	1.025				
L	0.45	0.61	0.55				
L1	0.25	0.55	0.40				
М	0.085	0.150	0.110				
а	0°	8°					
All Dimensions in mm							

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT23



Dimensions	Value (in mm)
С	2.0
Х	0.8
X1	1.35
Υ	0.9
Y1	2.9



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